Takhee Lee

List of Publications by Citations

333 papers	13,786 citations	61 h-index	106 g-index
384 ext. papers	15,183 ext. citations	8.1 avg, IF	6.53 L-index

#	Paper	IF	Citations
333	Molecular-Scale Electronics: From Concept to Function. *Chemical Reviews*, **2016**, 116, 4318-440	68.1	746
332	Observation of molecular orbital gating. *Nature*, **2009**, 462, 1039-43	50.4	617
331	Mechanism of electron conduction in self-assembled alkanethiol monolayer devices. *Physical Review B*, **2003**, 68,	3.3	504
330	Organic Resistive Memory Devices: Performance Enhancement, Integration, and Advanced Architectures. *Advanced Functional Materials*, **2011**, 21, 2806-2829	15.6	383
329	Single molecule electronic devices. *Advanced Materials*, **2011**, 23, 1583-608	24	380
328	Inelastic Electron Tunneling Spectroscopy of an Alkanedithiol Self-Assembled Monolayer. *Nano Letters*, **2004**, 4, 643-646	11.5	335
327	The application of graphene as electrodes in electrical and optical devices. *Nanotechnology*, **2012**, 23, 112001	3.4	265
326	Evolution of nanomorphology and anisotropic conductivity in solvent-modified PEDOT:PSS films for polymeric anodes of polymer solar cells. *Journal of Materials Chemistry*, **2009**, 19, 9045		255
325	Large-scale patterned multi-layer graphene films as transparent conducting electrodes for GaN light-emitting diodes. *Nanotechnology*, **2010**, 21, 175201	3.4	233
324	Tunable electronic transport characteristics of surface-architecture-controlled ZnO nanowire field effect transistors. *Nano Letters*, **2008**, 8, 950-6	11.5	216
323	Three-dimensional integration of organic resistive memory devices. *Advanced Materials*, **2010**, 22, 5048-52	24	184
322	Rewritable switching of one diode-one resistor nonvolatile organic memory devices. *Advanced Materials*, **2010**, 22, 1228-32	24	157
321	Flexible multilevel resistive memory with controlled charge trap B- and N-doped carbon nanotubes. *Nano Letters*, **2012**, 12, 2217-21	11.5	156
320	Electric stress-induced threshold voltage instability of multilayer MoS2 field effect transistors. *ACS Nano*, **2013**, 7, 7751-8	16.7	155
319	Electrical and Optical Characterization of MoS2 with Sulfur Vacancy Passivation by Treatment with Alkanethiol Molecules. *ACS Nano*, **2015**, 9, 8044-53	16.7	151
318	A new approach for molecular electronic junctions with a multilayer graphene electrode. *Advanced Materials*, **2011**, 23, 755-60	24	150
317	Stable switching characteristics of organic nonvolatile memory on a bent flexible substrate. *Advanced Materials*, **2010**, 22, 3071-5	24	148

316	Mechanically controllable break junctions for molecular electronics. *Advanced Materials*, **2013**, 25, 4845-67	24	147
315	Flexible molecular-scale electronic devices. *Nature Nanotechnology*, **2012**, 7, 438-42	28.7	144
314	All-Inkjet-Printed Organic Thin-Film Transistor Inverter on Flexible Plastic Substrate. *IEEE Electron Device Letters*, **2011**, 32, 1134-1136	4.4	137
313	Oxygen environmental and passivation effects on molybdenum disulfide field effect transistors. *Nanotechnology*, **2013**, 24, 095202	3.4	134
312	Direct Observation of Ag Filamentary Paths in Organic Resistive Memory Devices. *Advanced Functional Materials*, **2011**, 21, 3976-3981	15.6	128
311	Flexible organic memory devices with multilayer graphene electrodes. *ACS Nano*, **2011**, 5, 5995-6000	16.7	119
310	Comparison of Electronic Transport Characterization Methods for Alkanethiol Self-Assembled Monolayers *Journal of Physical Chemistry B*, **2004**, 108, 8742-8750	3.4	115
309	Electron tunnelling in self-assembled monolayers. *Reports on Progress in Physics*, **2005**, 68, 523-544	14.4	115
308	Enhanced charge injection in pentacene field-effect transistors with graphene electrodes. *Advanced Materials*, **2011**, 23, 100-5	24	112
307	Recent Progress in Inkjet-Printed Thin-Film Transistors. *Advanced Science*, **2019**, 6, 1801445	13.6	109
306	Flexible organic solar cells composed of P3HT:PCBM using chemically doped graphene electrodes. *Nanotechnology*, **2012**, 23, 344013	3.4	109
305	Conductance and vibrational states of single-molecule junctions controlled by mechanical stretching and material variation. *Physical Review Letters*, **2011**, 106, 196804	7.4	106
304	Efficient bulk-heterojunction photovoltaic cells with transparent multi-layer graphene electrodes. *Organic Electronics*, **2010**, 11, 1864-1869	3.5	106
303	Photoelectron spectroscopic imaging and device applications of large-area patternable single-layer MoS2 synthesized by chemical vapor deposition. *ACS Nano*, **2014**, 8, 4961-8	16.7	105
302	Statistical analysis of electronic properties of alkanethiols in metal□olecule□metal junctions. *Nanotechnology*, **2007**, 18, 315204	3.4	105
301	Elastic and Inelastic Electron Tunneling in Alkane Self-Assembled Monolayers. *Journal of Physical Chemistry B*, **2004**, 108, 18398-18407	3.4	105
300	Electronic skins for soft, compact, reversible assembly of wirelessly activated fully soft robots. *Science Robotics*, **2018**, 3,	18.6	104
299	Biogenic formation of photoactive arsenic-sulfide nanotubes by Shewanella sp. strain HN-41. *Proceedings of the National Academy of Sciences of the United States of America*, **2007**, 104, 20410-5	11.5	100

298	Organic resistive nonvolatile memory materials. *MRS Bulletin*, **2012**, 37, 144-149	3.2	96
297	One Transistor One Resistor Devices for Polymer Non-Volatile Memory Applications. *Advanced Materials*, **2009**, 21, 2497-2500	24	96
296	High-Yield Functional Molecular Electronic Devices. *ACS Nano*, **2017**, 11, 6511-6548	16.7	95
295	Unipolar nonvolatile memory devices with composites of poly(9-vinylcarbazole) and titanium dioxide nanoparticles. *Organic Electronics*, **2009**, 10, 473-477	3.5	91
294	Substrate thermal conductivity effect on heat dissipation and lifetime improvement of organic light-emitting diodes. *Applied Physics Letters*, **2009**, 94, 253302	3.4	89
293	Passivation effects on ZnO nanowire field effect transistors under oxygen, ambient, and vacuum environments. *Applied Physics Letters*, **2008**, 92, 263109	3.4	88
292	Tuning of a graphene-electrode work function to enhance the efficiency of organic bulk heterojunction photovoltaic cells with an inverted structure. *Applied Physics Letters*, **2010**, 97, 213301	3.4	87
291	Novel nonvolatile memory with multibit storage based on a ZnO nanowire transistor. *Nano Letters*, **2010**, 10, 4316-20	11.5	87
290	Morphology- and orientation-controlled gallium arsenide nanowires on silicon substrates. *Nano Letters*, **2007**, 7, 39-44	11.5	86
289	Intermolecular chain-to-chain tunneling in metal-alkanethiol-metal junctions. *Journal of the American Chemical Society*, **2007**, 129, 3806-7	16.4	86
288	Structural and electrical characterization of a block copolymer-based unipolar nonvolatile memory device. *Advanced Materials*, **2012**, 24, 385-90	24	85
287	Three-terminal single-molecule junctions formed by mechanically controllable break junctions with side gating. *Nano Letters*, **2013**, 13, 2809-13	11.5	85
286	Inkjet-printed stretchable silver electrode on wave structured elastomeric substrate. *Applied Physics Letters*, **2011**, 98, 153110	3.4	84
285	Irradiation effects of high-energy proton beams on MoS2 field effect transistors. *ACS Nano*, **2014**, 8, 2774-81	16.7	82
284	Enhancement of photodetection characteristics of MoS2 field effect transistors using surface treatment with copper phthalocyanine. *Nanoscale*, **2015**, 7, 18780-8	7.7	76
283	Surface relief gratings on poly(3-hexylthiophene) and fullerene blends for efficient organic solar cells. *Applied Physics Letters*, **2007**, 91, 173509	3.4	76
282	Piezoelectric Effect on the Electronic Transport Characteristics of ZnO Nanowire Field-Effect Transistors on Bent Flexible Substrates. *Advanced Materials*, **2008**, 20, 4557-4562	24	75
281	Graphene-Conducting Polymer Hybrid Transparent Electrodes for Efficient Organic Optoelectronic Devices. *Advanced Functional Materials*, **2014**, 24, 1847-1856	15.6	69

280	Enhancement of field emission transport by molecular tilt configuration in metal-molecule-metal junctions. *Journal of the American Chemical Society*, **2009**, 131, 5980-5	16.4	69
279	Organic nonvolatile memory devices with charge trapping multilayer graphene film. *Nanotechnology*, **2012**, 23, 105202	3.4	67
278	High-performance compliant thermoelectric generators with magnetically self-assembled soft heat conductors for self-powered wearable electronics. *Nature Communications*, **2020**, 11, 5948	17.4	67
277	Fabrication of TiO2 nanotubes by using electrodeposited ZnO nanorod template and their application to hybrid solar cells. *Electrochimica Acta*, **2008**, 53, 2560-2566	6.7	65
276	High-Performance Solution-Processed Organo-Metal Halide Perovskite Unipolar Resistive Memory Devices in a Cross-Bar Array Structure. *Advanced Materials*, **2019**, 31, e1804841	24	64
275	Reversible switching characteristics of polyfluorene-derivative single layer film for nonvolatile memory devices. *Applied Physics Letters*, **2008**, 92, 253308	3.4	64
274	Influence of metal-molecule contacts on decay coefficients and specific contact resistances in molecular junctions. *Physical Review B*, **2007**, 76,	3.3	63
273	Flexible molecular-scale electronic devices composed of diarylethene photoswitching molecules. *Advanced Materials*, **2014**, 26, 3968-73	24	61
272	Redox-Induced Asymmetric Electrical Characteristics of Ferrocene-Alkanethiolate Molecular Devices on Rigid and Flexible Substrates. *Advanced Functional Materials*, **2014**, 24, 2472-2480	15.6	59
271	Electrical Properties of Synthesized Large-Area MoS Field-Effect Transistors Fabricated with Inkjet-Printed Contacts. *ACS Nano*, **2016**, 10, 2819-26	16.7	58
270	P-type CuO and Cu2O transistors derived from a sol gel copper (II) acetate monohydrate precursor. *Thin Solid Films*, **2016**, 600, 157-161	2.2	58
269	Coherent Tunneling Transport in Molecular Junctions *Journal of Physical Chemistry C*, **2010**, 114, 20431-20435	3.8	58
268	Mechanism of electron conduction in self-assembled alkanethiol monolayer devices. *Annals of the New York Academy of Sciences*, **2003**, 1006, 21-35	6.5	57
267	Tuning of the electronic characteristics of ZnO nanowire field effect transistors by proton irradiation. *ACS Nano*, **2010**, 4, 811-8	16.7	56
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265	Solution-processed reduced graphene oxide films as electronic contacts for molecular monolayer junctions. *Angewandte Chemie - International Edition*, **2012**, 51, 108-12	16.4	54
264	Effects of Metal Molecule Contact and Molecular Structure on Molecular Electronic Conduction in Nonresonant Tunneling Regime: Alkyl versus Conjugated Molecules. *Journal of Physical Chemistry C* , **2008**, 112, 13010-13016	3.8	52
263	Realization of highly reproducible ZnO nanowire field effect transistors with n-channel depletion and enhancement modes. *Applied Physics Letters*, **2007**, 90, 243103	3.4	51

262	Enhancement of the light output of GaN-based ultraviolet light-emitting diodes by a one-dimensional nanopatterning process. *Applied Physics Letters*, **2006**, 88, 103505	3.4	51
261	Inkjet-printed stretchable single-walled carbon nanotube electrodes with excellent mechanical properties. *Applied Physics Letters*, **2014**, 104, 113103	3.4	50
260	Transient reverse current phenomenon in a p-n heterojunction comprised of poly(3,4-ethylene-dioxythiophene):poly(styrene-sulfonate) and ZnO nanowall. *Applied Physics Letters*, **2008**, 93, 123109	3.4	50
259	Radiation hardness of the electrical properties of carbon nanotube network field effect transistors under high-energy proton irradiation. *Nanotechnology*, **2006**, 17, 5675-80	3.4	50
258	Transparent Large-Area MoS Phototransistors with Inkjet-Printed Components on Flexible Platforms. *ACS Nano*, **2017**, 11, 10273-10280	16.7	49
257	Flexible high-performance all-inkjet-printed inverters: organo-compatible and stable interface engineering. *Advanced Materials*, **2013**, 25, 4773-7	24	49
256	Low frequency noise characterizations of ZnO nanowire field effect transistors. *Journal of Applied Physics*, **2007**, 101, 044313	2.5	49
255	A robust, gravure-printed, silver nanowire/metal oxide hybrid electrode for high-throughput patterned transparent conductors. *Journal of Materials Chemistry C*, **2016**, 4, 3248-3255	7.1	47
254	Enhancement of the light output of GaN-based light-emitting diodes with surface-patterned ITO electrodes by maskless wet-etching. *Solid-State Electronics*, **2007**, 51, 793-796	1.7	47
253	Enhancement in the photodetection of ZnO nanowires by introducing surface-roughness-induced traps. *Nanotechnology*, **2011**, 22, 205204	3.4	46
252	Electrical properties of ZnO nanowire field effect transistors by surface passivation. *Colloids and Surfaces A: Physicochemical and Engineering Aspects*, **2008**, 313-314, 378-382	5.1	46
251	Trap-mediated electronic transport properties of gate-tunable pentacene/MoS p-n heterojunction diodes. *Scientific Reports*, **2016**, 6, 36775	4.9	45
250	Recent Advances in Interface Engineering of Transition-Metal Dichalcogenides with Organic Molecules and Polymers. *ACS Nano*, **2019**, 13, 9713-9734	16.7	45
249	Thermal stability of multilayer graphene films synthesized by chemical vapor deposition and stained by metallic impurities. *Nanotechnology*, **2012**, 23, 075702	3.4	45
248	Hydrogen-induced morphotropic phase transformation of single-crystalline vanadium dioxide nanobeams. *Nano Letters*, **2013**, 13, 1822-8	11.5	45
247	Diameter-engineered SnO2 nanowires over contact-printed gold nanodots using size-controlled carbon nanopost array stamps. *ACS Nano*, **2010**, 4, 1829-36	16.7	45
246	Influence of surface structure on the phonon-assisted emission process in the ZnO nanowires grown on homoepitaxial films. *Applied Physics Letters*, **2009**, 94, 043103	3.4	44
245	Electrical transport characteristics through molecular layers. *Journal of Materials Chemistry*, **2011**, 21, 18117		43

244	Investigation of the Transition Voltage Spectra of Molecular Junctions Considering Frontier Molecular Orbitals and the Asymmetric Coupling Effect. *Journal of Physical Chemistry C*, **2011**, 115, 17979-17985	3.8	43
243	Electrical Properties of Surface-Tailored ZnO Nanowire Field-Effect Transistors. *IEEE Transactions on Electron Devices*, **2008**, 55, 3020-3029	2.9	43
242	Au nanoparticle-decorated graphene electrodes for GaN-based optoelectronic devices. *Applied Physics Letters*, **2012**, 101, 031115	3.4	42
241	Resistive switching characteristics of polymer non-volatile memory devices in a scalable via-hole structure. *Nanotechnology*, **2009**, 20, 025201	3.4	42
240	Enhanced Charge Injection Properties of Organic Field-Effect Transistor by Molecular Implantation Doping. *Advanced Materials*, **2019**, 31, e1806697	24	41
239	Electrical characterization of organic resistive memory with interfacial oxide layers formed by O2 plasma treatment. *Applied Physics Letters*, **2010**, 97, 063305	3.4	41
238	Graphene/Pentacene Barristor with Ion-Gel Gate Dielectric: Flexible Ambipolar Transistor with High Mobility and On/Off Ratio. *ACS Nano*, **2015**, 9, 7515-22	16.7	40
237	Contact-Engineered Electrical Properties of MoS Field-Effect Transistors via Selectively Deposited Thiol-Molecules. *Advanced Materials*, **2018**, 30, e1705540	24	39
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235	Electrical characterization of unipolar organic resistive memory devices scaled down by a direct metal-transfer method. *Advanced Materials*, **2011**, 23, 2104-7	24	38
234	Noise characteristics of charge tunneling via localized states in metal--molecule--metal junctions. *ACS Nano*, **2010**, 4, 4426-30	16.7	38
233	The effect of excimer laser annealing on ZnO nanowires and their field effect transistors. *Nanotechnology*, **2009**, 20, 095203	3.4	38
232	Electronic Properties of Metallic Nanoclusters on Semiconductor Surfaces: Implications for Nanoelectronic Device Applications. *Journal of Nanoparticle Research*, **2000**, 2, 345-362	2.3	38
231	Electronic transport in self-assembled alkanethiol monolayers. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 19, 117-125	3	36
230	Gate-bias stress-dependent photoconductive characteristics of multi-layer MoS2 field-effect transistors. *Nanotechnology*, **2014**, 25, 155201	3.4	35
229	Reversible Switching Phenomenon in Diarylethene Molecular Devices with Reduced Graphene Oxide Electrodes on Flexible Substrates. *Advanced Functional Materials*, **2015**, 25, 5918-5923	15.6	34
228	Vibrational spectra of metal-molecule-metal junctions in electromigrated nanogap electrodes by inelastic electron tunneling. *Applied Physics Letters*, **2009**, 94, 103110	3.4	34
227	Fabrication, structural and electrical characterization of VO2 nanowires. *Materials Research Bulletin*, **2008**, 43, 1649-1656	5.1	33

226	Graphene films show stable cell attachment and biocompatibility with electrogenic primary cardiac cells. *Molecules and Cells*, **2013**, 36, 577-82	3.5	32
225	InGaN-Based p-i-n Solar Cells with Graphene Electrodes. *Applied Physics Express*, **2011**, 4, 052302	2.4	32
224	Single-Atom Switches and Single-Atom Gaps Using Stretched Metal Nanowires. *ACS Nano*, **2016**, 10, 9695-9702	13.7	32
223	Resistive Switching Characteristics of Solution-Processed Transparent TiO[sub x] for Nonvolatile Memory Application. *Journal of the Electrochemical Society*, **2010**, 157, H1042	3.9	31
222	Logic inverters composed of controlled depletion-mode and enhancement-mode ZnO nanowire transistors. *Applied Physics Letters*, **2009**, 94, 173118	3.4	31
221	Nanoscale Resistive Switching of a Copper-Carbon-Mixed Layer for Nonvolatile Memory Applications. *IEEE Electron Device Letters*, **2009**, 30, 302-304	4.4	31
220	Hierarchical Porous Film with Layer-by-Layer Assembly of 2D Copper Nanosheets for Ultimate Electromagnetic Interference Shielding. *ACS Nano*, **2021**, 15, 829-839	16.7	31
219	One-Step Interface Engineering for All-Inkjet-Printed, All-Organic Components in Transparent, Flexible Transistors and Inverters: Polymer Binding. *ACS Applied Materials & Interfaces*, **2017**, 9, 8819-8829	9.5	29
218	Hybrid Complementary Logic Circuits of One-Dimensional Nanomaterials with Adjustment of Operation Voltage. *Advanced Materials*, **2009**, 21, 2156-2160	24	29
217	Structural and electrical characterization of intrinsic n-type In2O3 nanowires. *Colloids and Surfaces A: Physicochemical and Engineering Aspects*, **2008**, 313-314, 308-311	5.1	29
216	Investigation of Time-Dependent Resistive Switching Behaviors of Unipolar Nonvolatile Organic Memory Devices. *Advanced Functional Materials*, **2018**, 28, 1801162	15.6	28
215	Effect of gate bias sweep rate on the electronic properties of ZnO nanowire field-effect transistors under different environments. *Applied Physics Letters*, **2008**, 92, 233120	3.4	28
214	Random telegraph signals in n-type ZnO nanowire field effect transistors at low temperature. *Applied Physics Letters*, **2007**, 91, 053107	3.4	28
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212	Effect of PEDOT:PSS-molecule interface on the charge transport characteristics of the large-area molecular electronic junctions. *Organic Electronics*, **2012**, 13, 771-777	3.5	27
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210	Contact Resistance of Inkjet-Printed Silver Source-Drain Electrodes in Bottom-Contact OTFTs. *Journal of Display Technology*, **2012**, 8, 48-53		27
209	A self-assembled Ag nanoparticle agglomeration process on graphene for enhanced light output in GaN-based LEDs. *Nanotechnology*, **2012**, 23, 255201	3.4	27

208	Electrical conduction through self-assembled monolayers in molecular junctions: Au/molecules/Au versus Au/molecule/PEDOT:PSS/Au. *Thin Solid Films*, **2009**, 518, 824-828	2.2	27
207	Effects of channel-length scaling on In2O3 nanowire field effect transistors studied by conducting atomic force microscopy. *Applied Physics Letters*, **2007**, 90, 173106	3.4	27
206	Effects of surface roughness on the electrical characteristics of ZnO nanowire field effect transistors. *Applied Surface Science*, **2008**, 254, 7559-7564	6.7	27
205	Resistive switching characteristics of solution-processed TiOx for next-generation non-volatile memory application; transparency, flexibility, and nano-scale memory feasibility. *Microelectronic Engineering*, **2011**, 88, 1143-1147	2.5	26
204	High-performance organic charge trap flash memory devices based on ink-jet printed 6,13-bis(triisopropylsilylethynyl) pentacene transistors. *Applied Physics Letters*, **2010**, 96, 213107	3.4	25
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202	Layer-by-Layer Structural Identification of 2D Ruddlesden–Popper Hybrid Lead Iodide Perovskites by Solid-State NMR Spectroscopy. *Chemistry of Materials*, **2021**, 33, 370-377	9.6	25
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200	A study of graphene films synthesized on nickel substrates: existence and origin of small-base-area peaks. *Nanotechnology*, **2011**, 22, 045706	3.4	24
199	Controlled assembly of In2O3 nanowires on electronic circuits using scanning optical tweezers. *Optics Express*, **2009**, 17, 17491-501	3.3	24
198	High-fidelity formation of a molecular-junction device using a thickness-controlled bilayer architecture. *Small*, **2008**, 4, 1399-405	11	24
197	All-Inkjet-Printed Organic Thin-Film Transistors with Silver Gate, Source/Drain Electrodes. *Japanese Journal of Applied Physics*, **2011**, 50, 03CB05	1.4	24
196	Enhanced characteristics of pentacene field-effect transistors with graphene electrodes and substrate treatments. *Applied Physics Letters*, **2011**, 99, 083306	3.4	23
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194	An ohmic nanocontact to GaAs. *Applied Physics Letters*, **1999**, 74, 2869-2871	3.4	23
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189	Electronic properties associated with conformational changes in azobenzene-derivative molecular junctions. *Organic Electronics*, **2011**, 12, 2144-2150	3.5	22
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186	Effect of metal ions on the switching performance of polyfluorene-based organic non-volatile memory devices. *Organic Electronics*, **2010**, 11, 109-114	3.5	21
185	Improved photoswitching response times of MoS2 field-effect transistors by stacking p-type copper phthalocyanine layer. *Applied Physics Letters*, **2016**, 109, 183502	3.4	21
184	Electrical and structural properties of antimony-doped p-type ZnO nanorods with self-corrugated surfaces. *Nanotechnology*, **2012**, 23, 495712	3.4	20
183	Intrinsic charge transport of conjugated organic molecules in electromigrated nanogap junctions. *Journal of Applied Physics*, **2011**, 109, 102419	2.5	20
182	Removal of cetyltrimethylammonium bromide to enhance the biocompatibility of Au nanorods synthesized by a modified seed mediated growth process. *Journal of Nanoscience and Nanotechnology*, **2008**, 8, 4670-4	1.3	20
181	Inkjet-Printed Silver Gate Electrode and Organic Dielectric Materials for Bottom-Gate Pentacene Thin-Film Transistors. *Journal of the Korean Physical Society*, **2009**, 54, 518-522	0.6	20
180	Characterization of PI:PCBM organic nonvolatile resistive memory devices under thermal stress. *Organic Electronics*, **2016**, 33, 48-54	3.5	20
179	Large scale MoS 2 nanosheet logic circuits integrated by photolithography on glass. *2D Materials*, **2016**, 3, 044001	5.9	20
178	Highly Reliable Superhydrophobic Protection for Organic Field-Effect Transistors by Fluoroalkylsilane-Coated TiO Nanoparticles. *ACS Nano*, **2018**, 12, 11062-11069	16.7	20
177	High-performance inkjet-printed four-terminal microelectromechanical relays and inverters. *Nano Letters*, **2015**, 15, 3261-6	11.5	19
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175	Tuning of operation mode of ZnO nanowire field effect transistors by solvent-driven surface treatment. *Nanotechnology*, **2009**, 20, 475702	3.4	19
174	Templated assembly of metal nanoparticles in nanoimprinted patterns for metal nanowire fabrication. *Nanotechnology*, **2009**, 20, 355302	3.4	19
173	A direct metal transfer method for cross-bar type polymer non-volatile memory applications. *Nanotechnology*, **2008**, 19, 405201	3.4	19

172	A statistical method for determining intrinsic electronic transport properties of self-assembled alkanethiol monolayer devices. *Applied Physics Letters*, **2007**, 91, 253116	3.4	19
171	Origin of multi-level switching and telegraphic noise in organic nanocomposite memory devices. *Scientific Reports*, **2016**, 6, 33967	4.9	18
170	Large-area fabrication of periodic sub-15 nm-width single-layer graphene nanorings. *Advanced Materials*, **2013**, 25, 199-204	24	18
169	Atomic switches of metallic point contacts by plasmonic heating. *Light: Science and Applications*, **2019**, 8, 34	16.7	17
168	The application of orthogonal photolithography to micro-scale organic field effect transistors and complementary inverters on flexible substrate. *Applied Physics Letters*, **2014**, 104, 053301	3.4	17
167	Structural and photoluminescence characterization of ZnO nanowalls grown by metal organic chemical vapor deposition. *Thin Solid Films*, **2009**, 518, 865-869	2.2	17
166	Highly Stable Contact Doping in Organic Field Effect Transistors by Dopant-Blockade Method. *Advanced Functional Materials*, **2020**, 30, 2000058	15.6	17
165	A new approach for high-yield metal-molecule-metal junctions by direct metal transfer method. *Nanotechnology*, **2015**, 26, 025601	3.4	16
164	4K-bit and microlithographic integration of organic nonvolatile resistive memory devices. *Organic Electronics*, **2015**, 17, 192-197	3.5	16
163	Printing of sub-100-nm metal nanodot arrays by carbon nanopost stamps. *ACS Nano*, **2011**, 5, 5543-51	16.7	16
162	Flexible resistive random access memory using solution-processed TiOx with Al top electrode on Ag layer-inserted indium-zinc-tin-oxide-coated polyethersulfone substrate. *Applied Physics Letters*, **2011**, 99, 142110	3.4	16
161	Reliable Organic Nonvolatile Memory Device Using a Polyfluorene-Derivative Single-Layer Film. *IEEE Electron Device Letters*, **2008**, 29, 852-855	4.4	16
160	Ohmic nanocontacts to GaAs using undoped and p-doped layers of low-temperature-grown GaAs. *Applied Physics Letters*, **2000**, 76, 212-214	3.4	16
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